



### DMG4N60SK3

### 600V N-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

V <sub>(BR)DSS</sub> (@ T <sub>J</sub> Max)	R <sub>DS(ON)</sub> Max	I <sub>D</sub> T <sub>C</sub> = +25°C
650V	2.3Ω @ V <sub>GS</sub> = 10V	3.7A

### **Features**

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low Gate Input Resistance
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

### **Description**

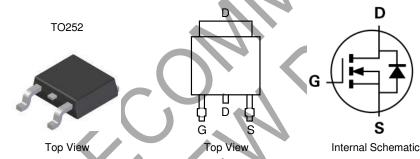
This new generation MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

## **Applications**

- Motor Control
- Backlighting
- DC-DC Converters
- Power Management Functions

## **Mechanical Data**

- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.33 grams (Approximate)



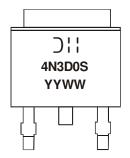
## Ordering Information (Note 4)

- 7				
	Part Number	Compliance	Case	Packaging
	DMG4N60SK3-13	Standard	TO252	2500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/guality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.</p>
  4. For packaging details, see http://www.diodes.com/products/packages.html.

## **Marking Information**



⊃ ¦ = Manufacturer's Marking 4N3D0S= Product Type Marking Code YYWW = Date Code Marking YY or YY= Last Digit of Year (ex: 14 = 2014) WW or WW= Week Code (01 to 53)



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	600	V
Gate-Source Voltage			V <sub>GSS</sub>	±30	V
Continuous Drain Current, V <sub>GS</sub> = 10V	Steady State	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I <sub>D</sub>	3.7 2.4	Α
Maximum Body Diode Forward Current			I <sub>S</sub>	3.7	Α
Pulsed Drain Current (10μs pulse, Duty Cycle = 1%)			I <sub>DM</sub>	5	Α
Avalanche Current, L = 60mH (Note 6)			I <sub>AS</sub>	1.7	Α
Avalanche Energy, L = 60mH (Note 6)	Avalanche Energy, L = 60mH (Note 6)			90	mJ

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	PD	48 19	W
Thermal Resistance, Junction to Ambient (Note 5)		R <sub>OJA</sub>	47	°C/W
Thermal Resistance, Junction to Case		R <sub>eJC</sub>	2.6	C/VV
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	600		1	V	$V_{GS} = 0V, I_{D} = 250\mu A$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		_	1	μΑ	$V_{DS} = 600V, V_{GS} = 0V$
Gate-Source Leakage	IGSS	_	_	100	nA	$V_{GS} = \pm 30V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)				*		
Gate Threshold Voltage	$V_{GS(TH)}$	2.5	3.5	4.5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>		2.0	2.3	Ω	$V_{GS} = 10V, I_D = 2A$
Diode Forward Voltage	$V_{SD}$	_	0.8	1.4	V	$V_{GS} = 0V, I_{S} = 1A$
DYNAMIC CHARACTERISTICS (Note 6)			•			
Input Capacitance	C <sub>iss</sub>		532			V <sub>DS</sub> = 25V, f = 1.0MHz,
Output Capacitance	$C_{oss}$		47	_	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	4	_		$V_{GS} = 0$
Gate Resistance	$R_{G}$	_	3.3	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge (V <sub>GS</sub> = 10V)	$Q_g$	_	14.3	_		1001/ 1
Gate-Source Charge	$Q_{gs}$	_	3.3	_	nC	$V_{DD} = 480V, I_{D} = 4A,$
Gate-Drain Charge	$Q_{gd}$	_	6.9	_		$V_{GS} = 10V$
Turn-On Delay Time	t <sub>D(ON)</sub>	_	14	_		
Turn-On Rise Time	t <sub>R</sub>	_	34	_		$V_{DD} = 300V, R_G = 25\Omega, I_D = 4A,$
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	32	_	ns	V <sub>GS</sub> = 10V
Turn-Off Fall Time	t <sub>F</sub>	_	25	_		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	229	_	ns	$dI/dt = 100A/\mu s$ , $V_{DS} = 100V$ ,
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	1	1564		nC	$I_F = 4A$

Notes:

- 5. Device mounted on FR-4 substrate PCB, 2oz copper, with 1inch square copper pad layout.6. Guaranteed by design. Not subject to production testing.7. Short duration pulse test used to minimize self-heating effect.



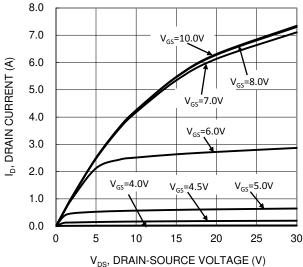


Figure 1. Typical Output Characteristic

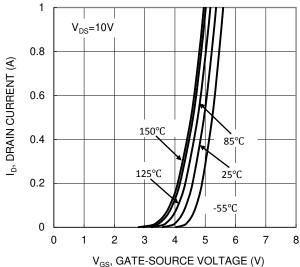


Figure 2. Typical Transfer Characteristic

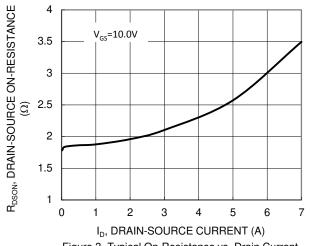


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

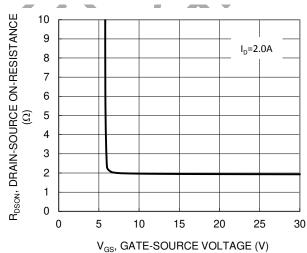


Figure 4. Typical Transfer Characteristic

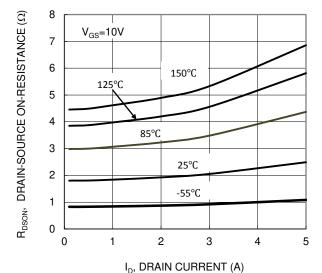


Figure 5. Typical On-Resistance vs Drain Current and Temperature

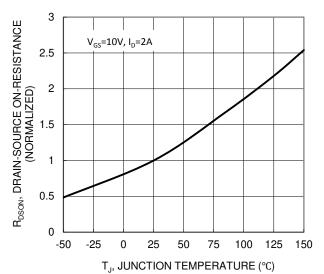


Figure 6. On-Resistance Variation with Temperature





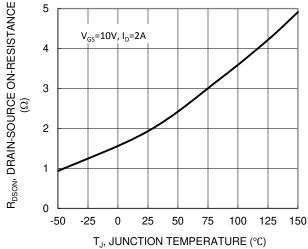
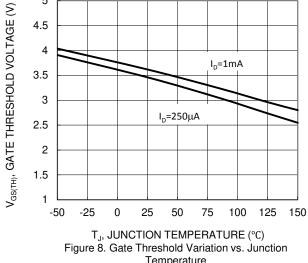


Figure 7. On-Resistance Variation with Temperature



5

Temperature

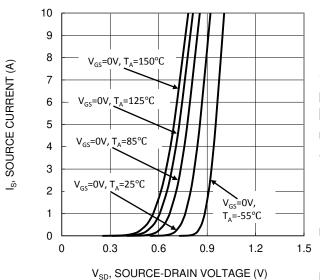


Figure 9. Diode Forward Voltage vs. Current

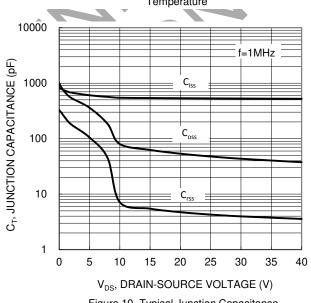
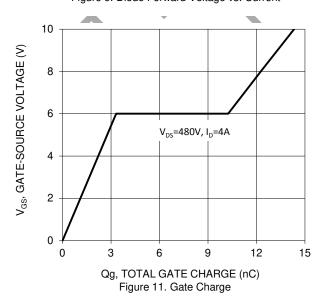
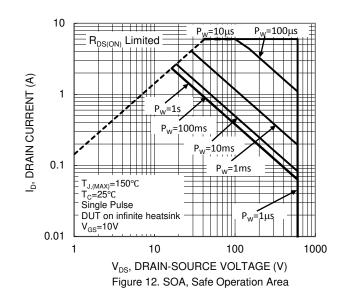
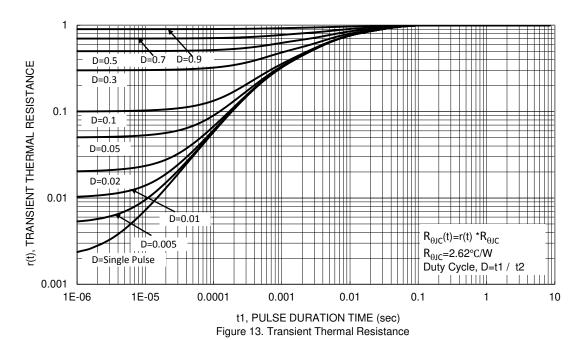


Figure 10. Typical Junction Capacitance





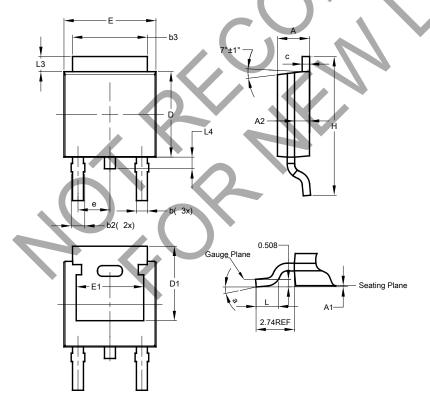




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### (1) Package Type: TO252 (DPAK)



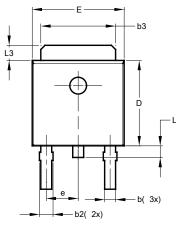
TO252 (DPAK)				
Dim	Min	Max	Тур	
Α	2.19	2.39	2.29	
<b>A</b> 1	0.00	0.13	0.08	
<b>A2</b>	0.97	1.17	1.07	
p	0.64	0.88	0.783	
b2	0.76	1.14	0.95	
b3	5.21	5.46	5.33	
C	0.45	0.58	0.531	
D	6.00	6.20	6.10	
D1	5.21	1	_	
Ф			2.286	
Е	6.45	6.70	6.58	
E1	4.32		_	
H	9.40	10.41	9.91	
Г	1.40	1.78	1.59	
L3	0.88	1.27	1.08	
L4	0.64	1.02	0.83	
а	0°	10°		
All Dimensions in mm				

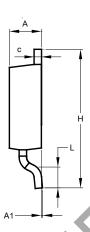


# Package Outline Dimensions (continued)

 $Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$ 

### (2) Package Type: TO252 (DPAK) (Type BR)

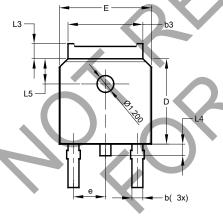


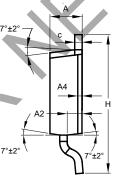


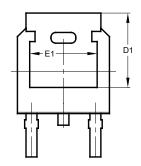
_	E1	) [ -		D1
	<del> </del>	<del> </del>	}	

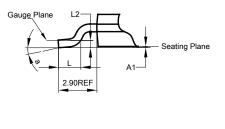
TO252 (DPAK)						
	(Type BR)					
Dim	Min	Max	Тур			
Α	2.20	2.40				
<b>A</b> 1	0.00	0.10	_			
p	0.50	0.70	_			
b3	5.20	5.40	_			
o	0.45	0.55				
D	5.95	6.25	1			
D1	5.10	5.50	_			
П	6.45	6.70	<b>\</b>			
E1	4.71	4.91	_			
a	2.24	2.34	_			
H	9.45	9.95	_			
7	1.25	1.75	_			
L3	0.95	1.25	_			
L4	0.60	0.90	_			
All Dimensions in mm						

### (3) Package Type: TO252 (DPAK) (Type TH)







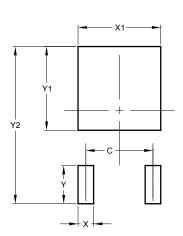


TO252 (DPAK)				
		e TH)		
Dim	Min	Max	Тур	
Α	2.20	2.38	2.30	
<b>A</b> 1	0.00	0.10		
<b>A2</b>	0.97	1.17	1.07	
<b>A</b> 4	0	.10 RE	F	
b	0.72	0.85	0.78	
b3	5.23	5.45	5.33	
С	0.47	0.58	0.53	
D	6.00	6.20	6.10	
D1	5	.30 RE	F	
е	2.	286 BS	C	
Е	6.50	6.70	6.60	
E1	4.70	4.92	4.83	
Н	9.90	10.10	10.30	
L	1.40	1.70	1.60	
L2	0.51 BSC			
L3	0.90	1.25		
L4	0.60	1.00	0.80	
L5	1.70	1.90	1.80	
а	0°	8°	_	
All Dimensions in mm				



## **Suggested Pad Layout**

 $Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$ 



### TO252 (DPAK)

Dimensions	Value (in mm)
С	4.572
X	1.060
X1	5.632
Υ	2.600
Y1	5.700
V2	10.700



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